

## **FJP5021**

### High Voltage and High Reliability

- High Speed Switching :  $t_F = 0.1 \mu s$  (Typ.)
- Wide SOA



1.Base 2.Collector 3.Emitter

### **NPN Silicon Transistor**

### **Absolute Maximum Ratings** $T_C=25^{\circ}C$ unless otherwise noted

| Symbol           | Parameter                                    | Value      | Units |  |
|------------------|--|------------|-------|--|
| V <sub>CBO</sub> | Collector-Base Voltage                       | 800        | V     |  |
| V <sub>CEO</sub> | Collector-Emitter Voltage                    | 500 V      |       |  |
| V <sub>EBO</sub> | Emitter-Base Voltage                         | 7          | V     |  |
| I <sub>C</sub>   | Collector Current (DC)                       | 5          | Α     |  |
| I <sub>CP</sub>  | Collector Current (Pulse)                    | 10         | Α     |  |
| I <sub>B</sub>   | Base Current                                 | 2          | Α     |  |
| P <sub>C</sub>   | Collector Dissipation (T <sub>C</sub> =25°C) | 50         | W     |  |
| TJ               | Junction Temperature                         | 150        | °C    |  |
| T <sub>STG</sub> | Storage Temperature                          | - 55 ~ 150 | °C    |  |

## Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

| Symbol                 | Parameter                            | Test Condition   | Min. | Тур. | Max. | Units |
|------------------------|--------------------------------------|--|------|------|------|-------|
| BV <sub>CBO</sub>      | Collector-Base Breakdown Voltage     | $I_{C} = 1 \text{mA}, I_{E} = 0$                           | 800  |      |      | V     |
| BV <sub>CEO</sub>      | Collector-Emitter Breakdown Voltage  | $I_C = 5mA, I_B = 0$                                       | 500  |      |      | V     |
| BV <sub>EBO</sub>      | Emitter-Base Breakdown Voltage       | $I_E = 1 \text{mA}, I_C = 0$                               | 7    |      |      | V     |
| V <sub>CEX</sub> (sus) | Collector-Emitter Sustaining Voltage | $I_C = 2.5A$ , $I_{B1} = -I_{B2} = 1A$<br>L = 1mH, Clamped | 500  |      |      | V     |
| I <sub>CBO</sub>       | Collector Cut-off Current            | $V_{CB} = 500V, I_{E} = 0$                                 |      |      | 10   | μΑ    |
| I <sub>EBO</sub>       | Emitter Cut-off Current              | $V_{EB} = 5V, I_{C} = 0$                                   |      |      | 10   | μΑ    |
| h <sub>FE1</sub>       | DC Current Gain                      | $V_{CE} = 5V, I_{C} = 0.6A$                                | 15   |      | 50   |       |
| h <sub>FE2</sub>       |                                      | $V_{CE} = 5V, I_{C} = 3A$                                  | 8    |      |      |       |
| V <sub>CE</sub> (sat)  | Collector-Emitter Saturation Voltage | $I_C = 3A, I_B = 0.6A$                                     |      |      | 1    | V     |
| V <sub>BE</sub> (sat)  | Base-Emitter Saturation Voltage      | $I_C = 3A, I_B = 0.6A$                                     |      |      | 1.5  | V     |
| C <sub>ob</sub>        | Output Capacitance                   | $V_{CB} = 10V, I_{E} = 0, f=1MHz$                          |      | 80   |      | pF    |
| f <sub>T</sub>         | Current Gain Bandwidth Product       | $V_{CE} = 10V, I_{C} = 0.6A$                               |      | 18   |      | MHz   |
| t <sub>ON</sub>        | Turn On Time                         | V <sub>CC</sub> = 200V                                     |      |      | 0.5  | μs    |
| t <sub>STG</sub>       | Storage Time                         | $I_C = 5I_{B1} = -2.5I_{B2} = 4A$                          |      |      | 3    | μs    |
| t <sub>F</sub>         | Fall Time                            | $R_L = 50\Omega$   |      | 0.1  | 0.3  | μs    |

## **h**<sub>FE</sub> Classification

| Classification   | R       | 0       | Y       |
|------------------|---------|---------|---------|
| h <sub>FE1</sub> | 15 ~ 30 | 20 ~ 40 | 30 ~ 50 |

## **Typical Characteristics**

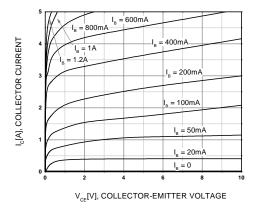


Figure 1. Static Characteristic

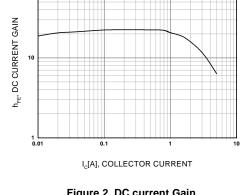


Figure 2. DC current Gain

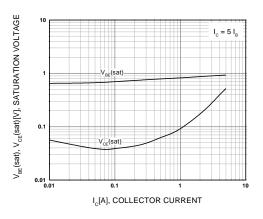


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

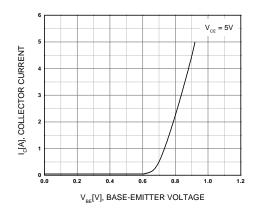


Figure 4. Base-Emitter On Voltage

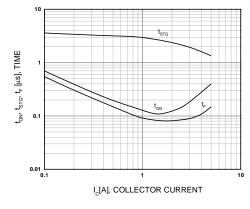


Figure 5. Switching Time

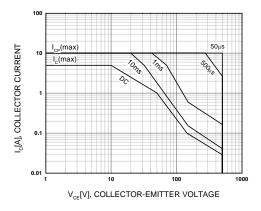


Figure 6. Forward Bias Safe Operating Area

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# Typical Characteristics (Continued)

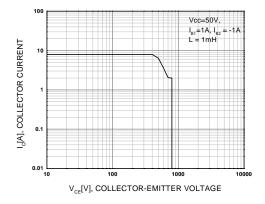


Figure 7. Reverse Bias Safe Operating Area

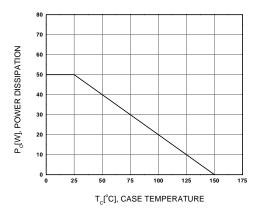
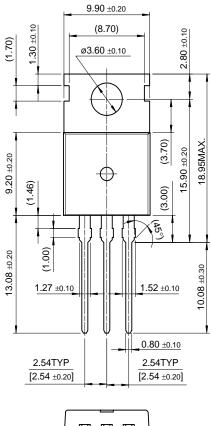
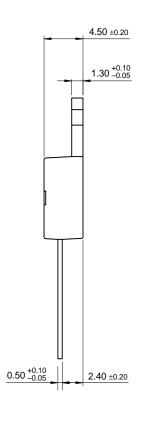


Figure 8. Power Derating

## **Package Dimensions**

## TO-220





10.00 ±0.20

Dimensions in Millimeters

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| CoolFET™             | FASTr™              | MicroFET™              | PowerTrench <sup>®</sup> | SuperSOT™-6            |
| CROSSVOLT™           | FRFET™              | MicroPak™              | QFET™                    | SuperSOT™-8            |
| DOME™                | GlobalOptoisolator™ | MICROWIRE™             | QS™                      | SyncFET™               |
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NPN Silicon Transistor

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Product status/pricing/packaging

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| Product    | Product status  | Pb-free Status     | Pricing* | Package type  | Leads | Packing method | Package Marking Convention**                                   |
|------------|-----------------|--------------------|----------|---------------|-------|----------------|--|
| FJP5021OTU | Full Production | Full<br>Production | \$0.55   | <u>TO-220</u> | 3     | . 8411         | Line 1: <b>\$Y</b> (Fairchild logo) Line 2: &3 Line 3: J5021-O |

<sup>\*</sup> Fairchild 1,000 piece Budgetary Pricing

<sup>\*\*</sup> A sample button will appear if the part is available through Fairchild's on-line samples program. If there is no sample button, please contact a Fairchild distributor to obtain samples



Indicates product with Pb-free second-level interconnect. For more information click here.

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